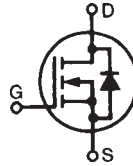


Polar™ HiPerFET™ Power MOSFET

IXFN56N90P

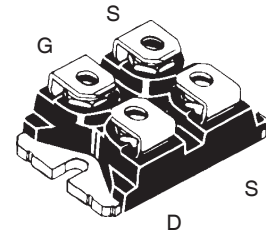
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$V_{DSS} = 900V$
 $I_{D25} = 56A$
 $R_{DS(on)} \leq 145m\Omega$
 $t_{rr} \leq 300ns$

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|------------------------|--------------------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 900 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 900 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 56 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 168 | A |
| I_A | $T_C = 25^\circ C$ | 28 | A |
| E_{AS} | $T_C = 25^\circ C$ | 2 | J |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 20 | V/ns |
| P_D | $T_C = 25^\circ C$ | 1000 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | 1.6mm (0.062 in.) from case for 10s | 300 | $^\circ C$ |
| V_{ISOL} | 50/60 Hz, RMS $I_{ISOL} \leq 1mA$ | $t = 1min$ $t = 1s$ | 2500 3000 V~ V~ |
| M_d | Mounting Torque Terminal Connection Torque | 1.5/13 1.3/11.5 | Nm/lb.in. Nm/lb.in. |
| Weight | | 30 | g |

miniBLOC
E153432



G = Gate
S = Source
D = Drain

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Low $R_{DS(on)}$ and Q_G
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier

Advantages

- High Power Density
- Easy to Mount
- Space Savings

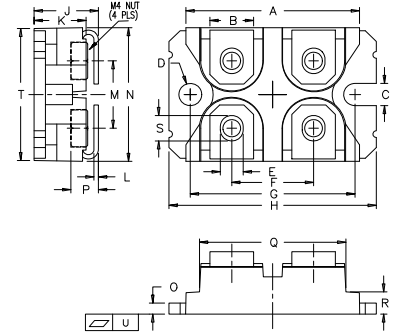
Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 8mA$ | 900 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 3mA$ | 3.5 | | 6.5 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 50 μA 5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 145 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|--|-----------------------|-------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1 | 27 | 44 | S |
| R_{Gi} | Gate Input Resistance | | 0.85 | Ω |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 23 | nF |
| C_{oss} | | | 1385 | pF |
| C_{rss} | | | 106 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External) | | 74 | ns |
| t_r | | | 80 | ns |
| $t_{d(off)}$ | | | 93 | ns |
| t_f | | | 38 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 375 | nC |
| Q_{gs} | | | 80 | nC |
| Q_{gd} | | | 145 | nC |
| R_{thJC} | | | 0.125 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.05 | | $^\circ\text{C/W}$ |

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

| SYM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 1.240 | 1.255 | 31.50 | 31.88 |
| B | .307 | .323 | 7.80 | 8.20 |
| C | .161 | .169 | 4.09 | 4.29 |
| D | .161 | .169 | 4.09 | 4.29 |
| E | .161 | .169 | 4.09 | 4.29 |
| F | .587 | .595 | 14.91 | 15.11 |
| G | 1.186 | 1.193 | 30.12 | 30.30 |
| H | 1.496 | 1.505 | 38.00 | 38.23 |
| J | .460 | .481 | 11.68 | 12.22 |
| K | .351 | .378 | 8.92 | 9.60 |
| L | .030 | .033 | 0.76 | 0.84 |
| M | .496 | .506 | 12.60 | 12.85 |
| N | .990 | 1.001 | 25.15 | 25.42 |
| O | .078 | .084 | 1.98 | 2.13 |
| P | .195 | .235 | 4.95 | 5.97 |
| Q | 1.045 | 1.059 | 26.54 | 26.90 |
| R | .155 | .174 | 3.94 | 4.42 |
| S | .186 | .191 | 4.72 | 4.85 |
| T | .968 | .987 | 24.59 | 25.07 |
| U | -.002 | .004 | -0.05 | 0.1 |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 56 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 224 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 0.5 \cdot I_{D25}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$ | | | 300 ns |
| Q_{RM} | | | 1.8 | μC |
| I_{RM} | | | 15 | A |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

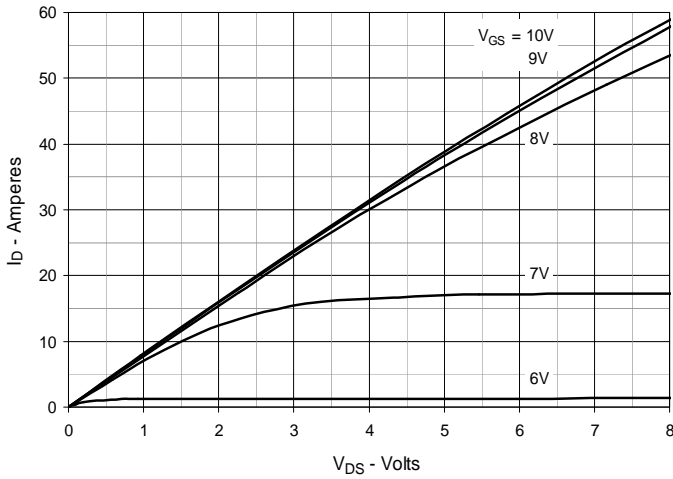
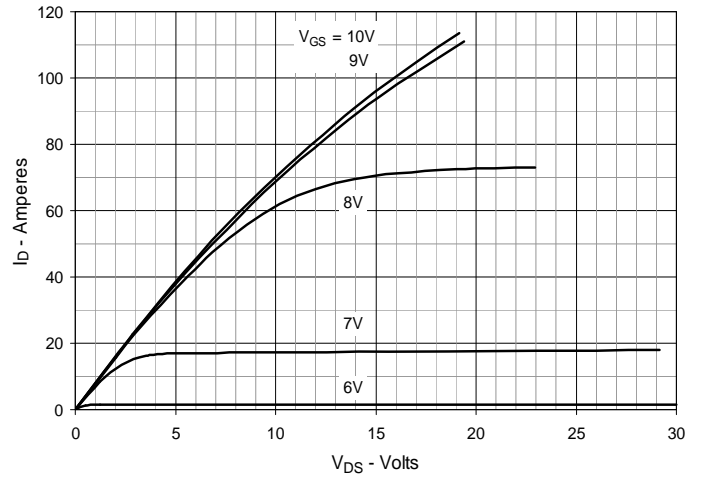
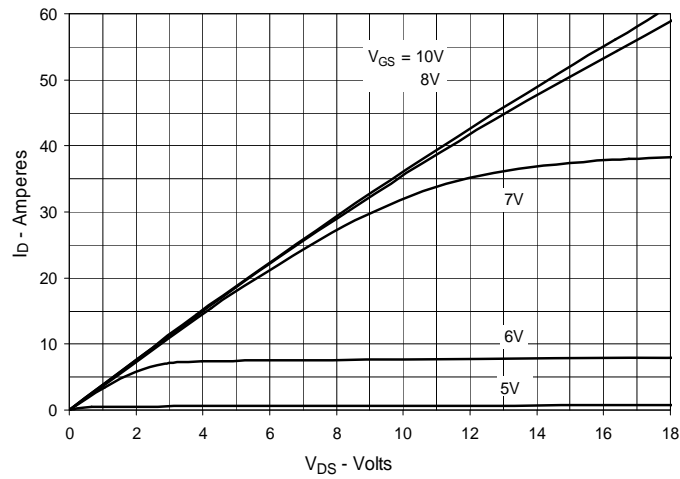
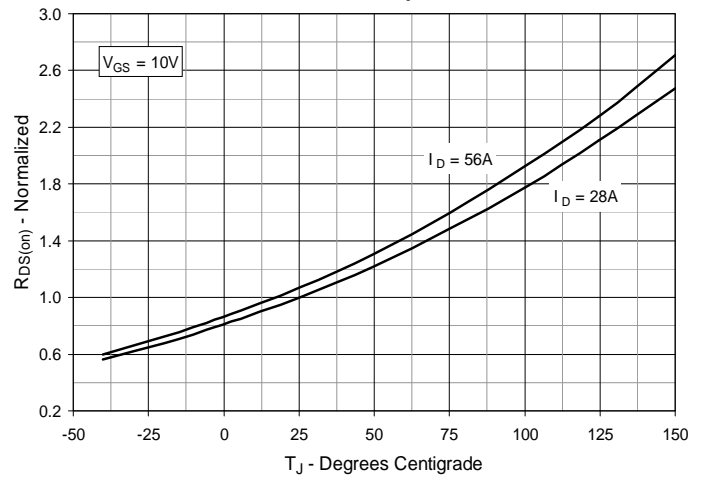
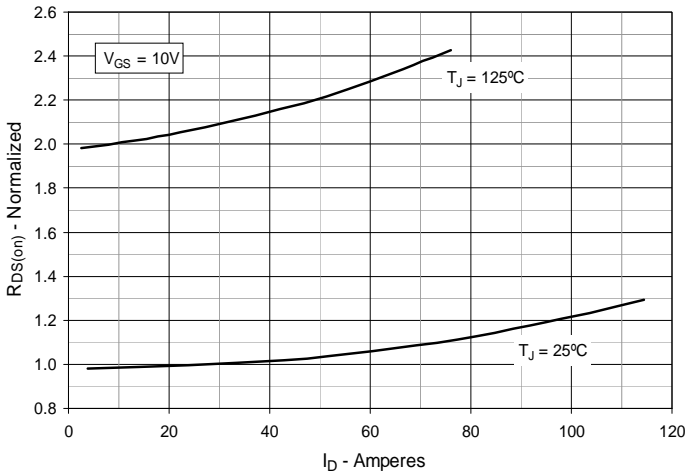
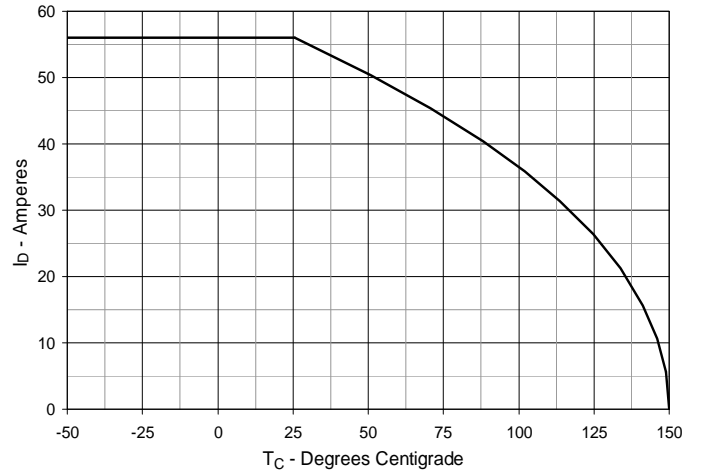
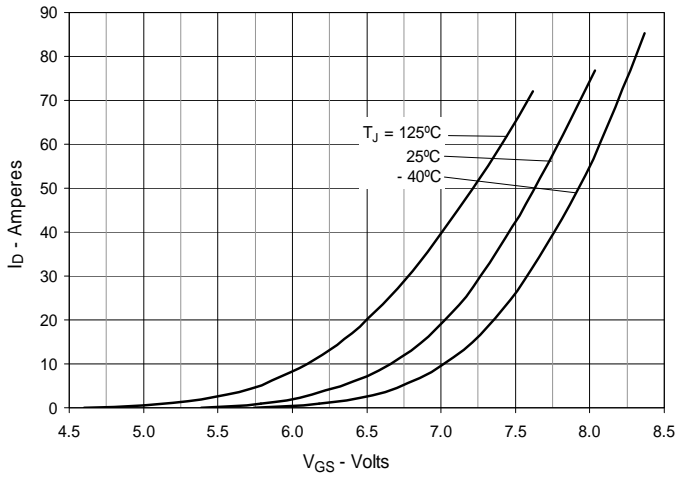
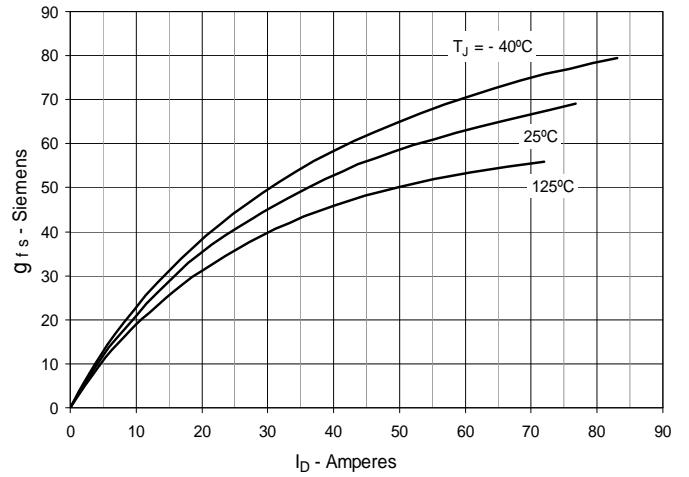
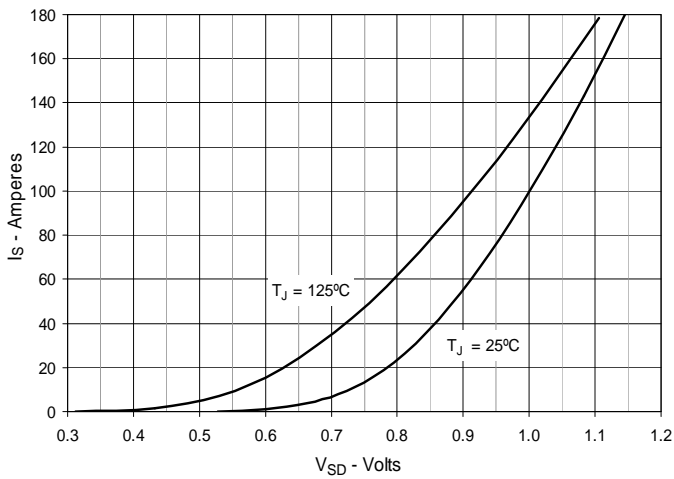
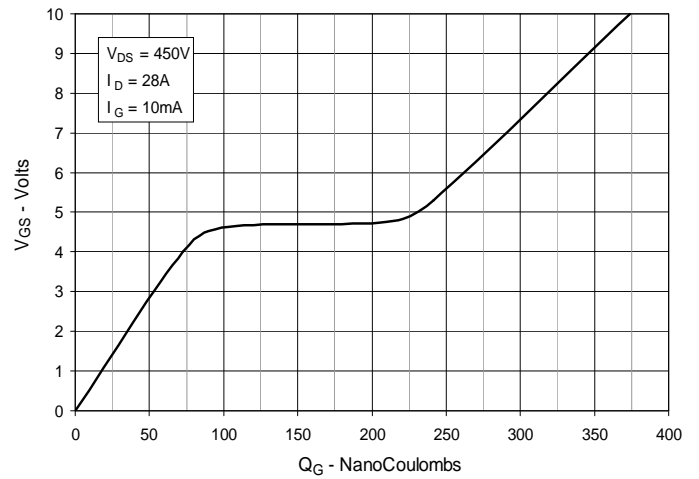
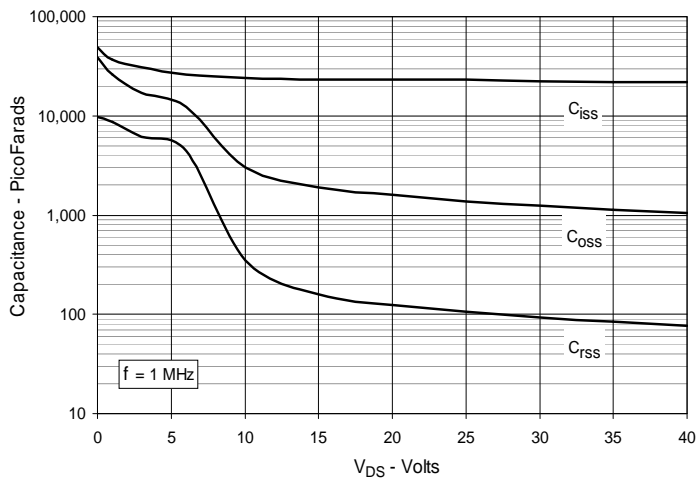
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 28\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 28\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance
